

## CLAIMS

1. A bipolar transistor, comprising:
  - a first semiconductor region of a first conductivity type defining a collector region;
  - a second semiconductor region of a second conductivity type defining a base region;
  - a third semiconductor region of said first conductivity type defining a emitter region; and
  - a metal layer providing contacts to said base and emitter regions;wherein the transistor has a specific area resistance less than about  $500\text{mOhms.mm}^2$ ; and
  - wherein said metal layer has a thickness greater than about  $3\mu\text{m}$ .
2. A bipolar transistor according to claim 1, wherein the metal layer has a thickness no less than  $4\mu\text{m}$ .
3. A bipolar transistor according to any preceding claim, wherein the metal layer has a thickness no less than  $6\mu\text{m}$ .
4. A bipolar transistor according to any preceding claim, wherein the emitter region defines a first surface, the base region extending to said surface in locations defined by apertures through emitter region, said metal layer overlying said first surface.
5. A bipolar transistor according to claim 4, wherein adjacent apertures are spaced less than  $100\mu\text{m}$  from each other.
6. A bipolar transistor substantially as hereinbefore defined, with reference to the accompanying drawing.